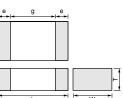
Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 6.3/16/25/50V





Part Number	Dimensions (mm)							
Part Number	L	W	Т	е	g min.			
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4			
GRM188*	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5			
GRM216		1.25 ±0.1	0.6 ±0.1	0.2 to 0.7	0.7			
GRM219	2.0 ±0.1		0.85 ±0.1					
GRM21B			1.25 ±0.1					
GRM319	2 2 +0 15	1.6 ±0.15	0.85 ±0.1					
GRM31M	3.2 ±0.15	1.0 ±0.15	1.15 ±0.1	0.3 to 0.8	1.5			
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2					

* Bulk Case : 1.6 ±0.07(L)×0.8 ±0.07(W)×0.8 ±0.07(T)

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R61A683KA01	X5R (EIA)	10	68000pF±10%	1.0	0.5	0.50
GRM155R61A104KA01	X5R (EIA)	10	0.1µF±10%	1.0	0.5	0.50
GRM188R61A334KA61	X5R (EIA)	10	0.33 µF±10%	1.6	0.8	0.80
GRM188R61A474KA61	X5R (EIA)	10	0.47µF±10%	1.6	0.8	0.80
GRM188R61A684KA61	X5R (EIA)	10	0.68µF±10%	1.6	0.8	0.80
GRM188R61A105KA61	X5R (EIA)	10	1μF ±10%	1.6	0.8	0.80
GRM188R60J105KA01	X5R (EIA)	6.3	1μF ±10%	1.6	0.8	0.80
GRM219R61A105KC01	X5R (EIA)	10	1μF ±10%	2.0	1.25	0.90
GRM21BR61A225KA01	X5R (EIA)	10	2.2μF ±10%	2.0	1.25	1.25
GRM219R60J155KC01	X5R (EIA)	6.3	1.5μF ±10%	2.0	1.25	0.90
GRM21BR60J225KA01	X5R (EIA)	6.3	2.2μF ±10%	2.0	1.25	1.25
GRM21BR60J335KA11	X5R (EIA)	6.3	$3.3 \mu F \pm 10\%$	2.0	1.25	1.25
GRM21BR60J475KA11	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	1.25
GRM319R61A225KC01	X5R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM31XR61A335KC12	X5R (EIA)	10	$3.3 \mu F \pm 10\%$	3.2	1.6	1.30
GRM31CR61A475KA01	X5R (EIA)	10	4.7μF ±10%	3.2	1.6	1.60
GRM31MR60J475KC11	X5R (EIA)	6.3	4.7μF ±10%	3.2	1.6	1.15
GRM31CR61A106KA01	X5R (EIA)	10	10µF ±10%	3.2	1.6	1.60
GRM31CR60J106KA01	X5R (EIA)	6.3	10µF ±10%	3.2	1.6	1.60
GRM31CR60J226ME20	X5R (EIA)	6.3	22µF ±20%	3.2	1.6	1.60
GRM32ER61A106KC01	X5R (EIA)	10	10µF ±10%	3.2	2.5	2.50
GRM55DR61H106KA01	X5R (EIA)	50	10µF ±10%	5.7	5.0	2.00
GRM15XR71H221KA86	X7R (EIA)	50	220pF±10%	1.0	0.5	0.25
GRM155R71H221KA01	X7R (EIA)	50	220pF±10%	1.0	0.5	0.50
GRM15XR71H331KA86	X7R (EIA)	50	330pF±10%	1.0	0.5	0.25
GRM155R71H331KA01	X7R (EIA)	50	330pF±10%	1.0	0.5	0.50
GRM15XR71H471KA86	X7R (EIA)	50	470pF±10%	1.0	0.5	0.25
GRM155R71H471KA01	X7R (EIA)	50	470pF±10%	1.0	0.5	0.50
GRM15XR71H681KA86	X7R (EIA)	50	680pF±10%	1.0	0.5	0.25
GRM155R71H681KA01	X7R (EIA)	50	680pF±10%	1.0	0.5	0.50
GRM15XR71H102KA86	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.25
GRM155R71H102KA01	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.50
GRM15XR71H152KA86	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.25
GRM155R71H152KA01	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.50
GRM155R71H222KA01	X7R (EIA)	50	2200pF±10%	1.0	0.5	0.50

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Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R71H332KA01	X7R (EIA)	50	3300pF±10%	1.0	0.5	0.50
GRM155R71H472KA01	X7R (EIA)	50	4700pF±10%	1.0	0.5	0.50
GRM15XR71E182KA86	X7R (EIA)	25	1800pF±10%	1.0	0.5	0.25
GRM15XR71E222KA86	X7R (EIA)	25	2200pF±10%	1.0	0.5	0.25
GRM155R71E682KA01	X7R (EIA)	25	6800pF±10%	1.0	0.5	0.50
GRM155R71E103KA01	X7R (EIA)	25	10000pF±10%	1.0	0.5	0.50
GRM15XR71C332KA86	X7R (EIA)	16	3300pF±10%	1.0	0.5	0.25
GRM15XR71C472KA86	X7R (EIA)	16	4700pF±10%	1.0	0.5	0.25
GRM15XR71C682KA86	X7R (EIA)	16	6800pF±10%	1.0	0.5	0.25
GRM155R71C153KA01	X7R (EIA)	16	15000pF±10%	1.0	0.5	0.50
GRM155R71C223KA01	X7R (EIA)	16	22000pF±10%	1.0	0.5	0.50
GRM155R71A333KA01	X7R (EIA)	10	33000pF±10%	1.0	0.5	0.50
GRM155R71A473KA01	X7R (EIA)	10	47000pF±10%	1.0	0.5	0.50
GRM188R71H221KA01	X7R (EIA)	50	220pF±10%	1.6	0.8	0.80
GRM188R71H331KA01	X7R (EIA)	50	330pF±10%	1.6	0.8	0.80
GRM188R71H471KA01	X7R (EIA)	50	470pF±10%	1.6	0.8	0.80
RM188R71H681KA01	X7R (EIA)	50	680pF±10%	1.6	0.8	0.80
GRM188R71H102KA01	X7R (EIA)	50	1000pF±10%	1.6	0.8	0.80
GRM188R71H152KA01		50		1.6	0.8	0.80
GRM188R71H152KA01 GRM188R71H222KA01	X7R (EIA)		1500pF±10%			
	X7R (EIA)	50	2200pF±10%	1.6	0.8	0.80
GRM188R71H332KA01	X7R (EIA)	50	3300pF±10%	1.6	0.8	0.80
SRM188R71H472KA01	X7R (EIA)	50	4700pF±10%	1.6	0.8	0.80
GRM188R71H682KA01	X7R (EIA)	50	6800pF±10%	1.6	0.8	0.80
RM188R71H103KA01	X7R (EIA)	50	10000pF±10%	1.6	0.8	0.80
RM188R71H153KA01	X7R (EIA)	50	15000pF±10%	1.6	0.8	0.80
GRM188R71H223KA01	X7R (EIA)	50	22000pF±10%	1.6	0.8	0.80
GRM188R71E333KA01	X7R (EIA)	25	33000pF±10%	1.6	0.8	0.80
GRM188R71E473KA01	X7R (EIA)	25	47000pF±10%	1.6	0.8	0.80
GRM188R71E683KA01	X7R (EIA)	25	68000pF±10%	1.6	0.8	0.80
GRM188R71E104KA01	X7R (EIA)	25	0.1µF±10%	1.6	0.8	0.80
GRM188R71C104KA01	X7R (EIA)	16	0.1µF±10%	1.6	0.8	0.80
GRM188R71A154KA01	X7R (EIA)	10	0.15µF±10%	1.6	0.8	0.80
GRM188R71A224KA01	X7R (EIA)	10	22000pF±10%	1.6	0.8	0.80
GRM219R71H333KA01	X7R (EIA)	50	33000pF±10%	2.0	1.25	0.90
GRM21BR71H473KA01	X7R (EIA)	50	47000pF±10%	2.0	1.25	1.25
GRM21BR71H683KA01	X7R (EIA)	50	68000pF±10%	2.0	1.25	1.25
GRM21BR71H104KA01	X7R (EIA)	50	0.1µF±10%	2.0	1.25	1.25
GRM21BR71H154KA01	X7R (EIA)	50	0.15µF±10%	2.0	1.25	1.25
GRM21BR71H224KA01	X7R (EIA)	50	22000pF±10%	2.0	1.25	1.25
GRM21BR71E104KA01	X7R (EIA)	25	0.1µF±10%	2.0	1.25	1.25
GRM21BR71E154KA01	X7R (EIA)	25	0.15µF±10%	2.0	1.25	1.25
GRM219R71E224KC01	X7R (EIA)	25	22000pF±10%	2.0	1.25	0.90
GRM21BR71E334KC01	X7R (EIA)	25	0.33 μF±10%	2.0	1.25	1.25
GRM21BR71E474KC01	X7R (EIA)	25	0.47μF±10%	2.0	1.25	1.25
GRM219R71C474KC01	X7R (EIA)	16	0.47μF±10%	2.0	1.25	0.90
RM219R71C684KC01	X7R (EIA)	16	0.68µF±10%	2.0	1.25	0.90
RM21BR71C105KA01	X7R (EIA)	16	1μF ±10%	2.0	1.25	1.25
RM319R71H334KA01	X7R (EIA)	50	0.33 μF±10%	3.2	1.25	0.90
				3.2		
GRM31MR71H474KA01	X7R (EIA)	50	0.47µF±10%		1.6	1.15
GRM319R71E684KC01	X7R (EIA)	25	0.68µF±10%	3.2	1.6	0.90
SRM31MR71E105KC01	X7R (EIA)	25	1μF ±10%	3.2	1.6	1.15
GRM319R71C105KC11	X7R (EIA)	16	1μF ±10%	3.2	1.6	0.90
GRM31MR71C155KC11	X7R (EIA)	16	1.5μF ±10%	3.2	1.6	1.15
GRM31MR71C225KA35	X7R (EIA)	16	2.2µF ±10%	3.2	1.6	1.15
GRM319R71A105KC01	X7R (EIA)	10	1μF ±10%	3.2	1.6	0.90

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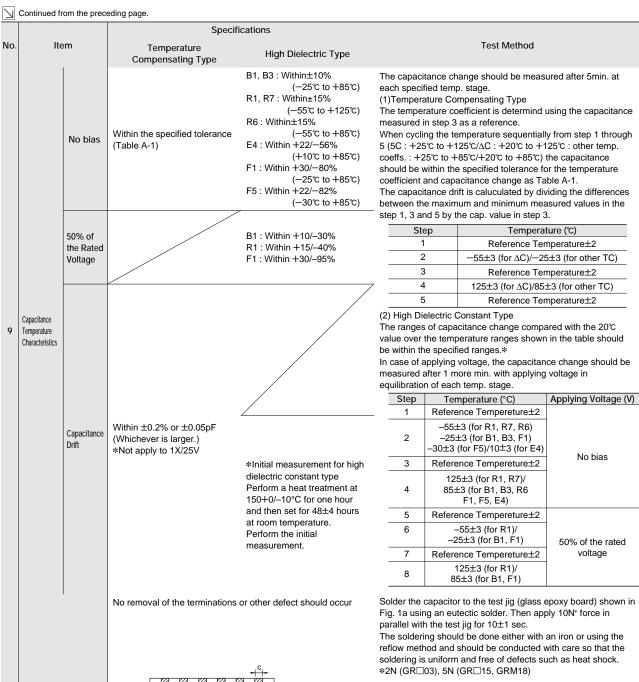
Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM319R71A225KA01	X7R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM32NR71H684KA01	X7R (EIA)	50	0.68µF±10%	3.2	2.5	1.35
GRM32RR71H105KA01	X7R (EIA)	50	1μF ±10%	3.2	2.5	1.80
GRM32RR71E225KC01	X7R (EIA)	25	2.2µF ±10%	3.2	2.5	1.80
GRM32MR71C225KC01	X7R (EIA)	16	2.2µF ±10%	3.2	2.5	1.15
GRM32NR71C335KC01	X7R (EIA)	16	3.3µF ±10%	3.2	2.5	1.35
GRM32RR71C475KC01	X7R (EIA)	16	4.7μF ±10%	3.2	2.5	1.80
GRM43ER71H225KA01	X7R (EIA)	50	2.2µF ±10%	4.5	3.2	2.50
GRM55RR71H105KA01	X7R (EIA)	50	1μF ±10%	5.7	5.0	1.80
GRM55RR71H155KA01	X7R (EIA)	50	1.5μF ±10%	5.7	5.0	1.80
GRM155F51H222ZA01	Y5V (EIA)	50	2200pF +80%, -20%	1.0	0.5	0.50
GRM155F51H472ZA01	Y5V (EIA)	50	4700pF +80%, -20%	1.0	0.5	0.50
GRM155F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.0	0.5	0.50
GRM155F51E223ZA01	Y5V (EIA)	25	22000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C473ZA01	Y5V (EIA)	16	47000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C104ZA01	Y5V (EIA)	16	10000pF +80%, -20%	1.0	0.5	0.50
GRM188F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H223ZA01	Y5V (EIA)	50	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H473ZA01	Y5V (EIA)	50	47000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51E104ZA01		25	10000pF +80%, -20%	1.6	0.8	0.80
	Y5V (EIA)					
GRM188F51C224ZA01	Y5V (EIA)	16	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C474ZA01	Y5V (EIA)	16	0.47µF +80%, -20%	1.6	0.8	0.80
GRM188F51A474ZC01	Y5V (EIA)	10	0.47µF +80%, -20%	1.6	0.8	0.80
GRM188F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	1.6	0.8	0.80
GRM219F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51H224ZA01	Y5V (EIA)	50	22000pF +80%, -20%	2.0	1.25	1.25
GRM219F51E224ZA01	Y5V (EIA)	25	22000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51E474ZA01	Y5V (EIA)	25	0.47µF +80%, -20%	2.0	1.25	1.25
GRM219F51E105ZA01	Y5V (EIA)	25	1µF +80%, -20%	2.0	1.25	0.90
GRM21BF51E225ZA01	Y5V (EIA)	25	2.2µF +80%, -20%	2.0	1.25	1.25
GRM219F51C105ZA01	Y5V (EIA)	16	1µF +80%, -20%	2.0	1.25	0.90
GRM21BF51C225ZA01	Y5V (EIA)	16	2.2µF +80%, -20%	2.0	1.25	1.25
GRM219F51A105ZA01	Y5V (EIA)	10	1µF +80%, -20%	2.0	1.25	0.90
GRM21BF51A225ZA01	Y5V (EIA)	10	2.2µF +80%, -20%	2.0	1.25	1.25
GRM21BF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	2.0	1.25	1.25
GRM31MF51H474ZA01	Y5V (EIA)	50	0.47µF +80%, -20%	3.2	1.6	1.15
GRM31MF51E105ZA01	Y5V (EIA)	25	1µF +80%, -20%	3.2	1.6	1.15
GRM31MF51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51C105ZA01	Y5V (EIA)	16	1µF +80%, -20%	3.2	1.6	0.90
GRM31MF51C225ZA01	Y5V (EIA)	16	2.2µF +80%, -20%	3.2	1.6	1.15
GRM31MF51C475ZA12	Y5V (EIA)	16	4.7µF +80%, -20%	3.2	1.6	1.15
GRM319F51A225ZA01	Y5V (EIA)	10	2.2µF +80%, -20%	3.2	1.6	0.90
GRM31MF51A475ZA01	Y5V (EIA)	10	4.7µF +80%, -20%	3.2	1.6	1.15
GRM31MF51A106ZA01	Y5V (EIA)	10	10µF +80%, -20%	3.2	1.6	1.15
GRM31MF50J106ZA01	Y5V (EIA)	6.3	10µF +80%, -20%	3.2	1.6	1.15
GRM32RF51H105ZA01	Y5V (EIA)	50	1µF +80%, -20%	3.2	2.5	1.80
GRM329F51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	2.5	0.90
GRM32NF51E106ZA01	Y5V (EIA)	25	10μF +80%, -20%	3.2	2.5	1.35
GRM32NF51C106ZA01	Y5V (EIA)	16	10μF +80%, -20%	3.2	2.5	1.35
GRM188E41H103MA01	Z5U (EIA)	50	10000pF±20%	1.6	0.8	0.80
GRM188E41H223MA01	Z5U (EIA)	50	22000pF±20%	1.6	0.8	0.80
GRM216E41H473MA01	Z5U (EIA)	50	47000pF±20%	2.0	1.25	0.60
GRM219E41H104MA01	Z5U (EIA)	50	10000pF±20%	2.0	1.25	0.90
	200 (LIA)	50	22000pF±20%	2.0	1.20	0.70

Specifications and Test Methods

		Specifi	cations				
No.	Item	Temperature Compensating Type	High Dielectric Type		Test	Method	
1	Operating Temperature Range	−55 to +125℃	B1, B3, F1 : -25°C to +85°C R1, R7 : -55°C to +125°C E4 : +10°C to +85°C F5 : -30°C to +85°C	Reference Tem $(2\Delta, 3\Delta, 4\Delta, B1)$			
2	Rated Voltage	See the previous pages		The rated voltage may be applied When AC voltage whichever is lar voltage range.	continuously to ge is superimpo	o the capacitor. osed on DC volt	age, V ^{P-P} or V ^{O-P} ,
3	Appearance	No defects or abnormalities		Visual inspection	n		
4	Dimensions	Within the specified dimensions	Using calipers				
5	Dielectric Strength	No defects or abnormalities	No failure should be observed when 300% of the rated voltage (temperature compensating type) or 250% of the rated voltage (high dielectric constant type) is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.				
6	Insulation Resistance	C≦0.047µF : More than 10,000 C>0.047µF : 500Ω • F	The insulation r voltage not exc 75%RH max. a charge/discharg	eeding the rate nd within 2 min	d voltage at 20° utes of charging	C/25℃ and	
7	Capacitance	Within the specified tolerance					20℃/25℃ at the
8	Q/ Dissipation Factor (D.F.)	30pF and over : Q≧1000 30pF and below : Q≧400+20C C : Nominal Capacitance (pF)	$ \begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.025max. \\ W.V.: 16/10V: 0.035max. \\ W.V.: 6.3V/4V \\ : 0.05max. (C<3.3\muF) \\ : 0.1max. (C\geq3.3\muF) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.05max. (C<0.1\muF) \\ : 0.09max. (C\geq0.1\muF) \\ W.V.: 16V/10V: 0.125max. \\ W.V.: 6.3V: 0.15max. \\ \end{array} $	Item Frequency	AC to ΔU, 1X (1000pF and below) 1±0.1MHz 0.5 to 5Vrms	ΔC to ΔU, 1X (more than 1000pF) R6, R7, F5 B1, B3, F1 1±0.1kHz 1±0.2Vrms	E4 1±0.1kHz 0.5±0.05Vrms

Continued on the following page.

Capacitors muRata



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Fig. 1a

 ∇

soldering is uniform and free of defects such as heat shock. (in mm) Туре b с а GR□03 0.3 0.9 0.3 **GR**[]15 0.4 1.5 0.5 GRM18 1.0 3.0 1.2 GRM21 1.2 4.0 1.65 2.2 5.0 GRM31 2.0 GRM32 2.2 5.0 2.9

3.5

4.5

GRM43

GRM55

Continued on the following page.

3.7

5.6

7.0

8.0

①Note • This catalog has only typical specifications because there is no space for detailed specifications. Therefore, please approve our product specification or transact the approval sheet for product specification before ordering. Especially, please read rating and ①CAUTION (for storage and operating, rating, soldering and mounting, handling) in them to prevent smoking and/or burning, etc.
 You are able to read a detailed specification in the website (http://search.murata.co.jp/) before to require our product specification or to transact the approval sheet for product specification.

ler resist

copper foil

Baked electrode or

Adhesive Strength

of Termination

Continued from the preceding page.

10		-	·	cations	-	Tool Mathead		
No.	Ite	em	Temperature Compensating Type	High Dielectric Type		Test Method		
		Appearance	No defects or abnormalities					
1	Vibration Resistance	Q/D.F.	Within the specified tolerance 30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V. : 25Vmin. : 0.025max. W.V. : 16/10V : 0.035max. W.V. : 6.3V/4V : 0.05max. (C<3.3µF) : 0.1max. (C≥3.3µF) [F1, F5] W.V. : 25Vmin. : 0.05max. (C<0.1µF) : 0.09max. (C≥0.1µF) W.V. : 16V/10V : 0.125max. W.V. : 6.3V : 0.15max.	in Fig. 2a using an eutectic solder. Then apply a force in the			
			No crack or marked defect shou	in Fig. 2a using direction show done either wit	Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 2a using an eutectic solder. Then apply a force in the direction shown in Fig. 3a for 5±1sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free			
2	Defle	ction	R230	0 Pressurizing speed : 1.0mm/sec. Pressurize Flexure : ≤1 neter 45	Type GR□03 GR□15 GRM18 GRM21 GRM31 GRM32 GRM43 GRM55	Image: height of the second	$\begin{array}{c ccc} 0 & 0.3 \\ \hline 5 & 0.5 \\ \hline 0 & 1.2 \\ \hline 0 & 1.65 \\ \hline 0 & 2.0 \\ \hline 0 & 2.9 \\ \hline 0 & 3.7 \\ \end{array}$	
13	Solderabi Terminati	5	75% of the terminations are to b continuously	(in mm) Immerse the capacitor in a solution of ethanol (JIS-K-8101) and rosin (JIS-K-5902) (25% rosin in weight propotion) . Preheat at 80 to 120°C for 10 to 30 seconds. After preheating, immerse in an eutectic solder solution for 2 ± 0.5 seconds at 230 ± 5 °C.				
			The measured and observed ch specifications in the following ta		_			
		Appearance Capacitance Change	No defects or abnormalities Within $\pm 2.5\%$ or ± 0.25 pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Immerse the c	pacitor at 120 to 150°C for apacitor in an eutectic sold conds. Set at room tempera	er solution at 270±5%	
14	Resistance to Soldering Heat	Q/D.F.	$\begin{array}{c} \text{[B1, B3, R1, R6, R7, E4]}\\ \text{(temperature compensating tyce) or 48}\\ \text{(software and below:}\\ \text{Q} \geq 400+20C \\ \text{C: Nominal Capacitance (pF)} \end{array} \begin{array}{c} \text{[B1, B3, R1, R6, R7, E4]}\\ \text{W.V.: 25Vmin. : 0.025max.}\\ \text{W.V.: 16/10V : 0.035max.}\\ \text{W.V.: 6.3V/4V}\\ \text{: 0.05max. (C<3.3\muF)}\\ \text{initial measurement for high dielectric or the set at room temperature for 48\pm44\\ \text{Perform a heat treatment at 150+0/-10}\\ \text{then set at room temperature for 48\pm44\\ \text{Perform the initial measurement.} \end{array} \begin{array}{c} \text{Initial measurement for high dielectric or the set at room temperature for 48\pm44\\ \text{Perform a heat treatment at 150+0/-10}\\ \text{then set at room temperature for 48\pm44\\ \text{Perform the initial measurement.} \end{array}$		compensating tyoe) or 48±, , then measure. ement for high dielectric cc t treatment at 150+0/-10° m temperature for 48±4 ho itial measurement. r GRM32/43/55	4 hours (high dielectri onstant type C for one hour and ours.		
				: 0.09max. (C≧0.1µF) W.V. : 16V/10V : 0.125max.	Step 1	Temperature 100℃ to 120℃	Time 1 min.	
				W.V. : 6.3V : 0.15max.	2	170°C to 200°C	1 min.	
		I.R.	More than 10,000M Ω or 500 Ω -	F (Whichever is smaller)				
		Dielectric	No defects					

Continued from the preceding page.

			Specifi	cations					
No.	Ite	em	Temperature Compensating Type	High Dielectric Type		Tes	t Method	ł	
			The measured and observed ch specifications in the following ta						
		Appearance	No defects or abnormalities						
		Capacitance Change	Within $\pm 2.5\%$ or ± 0.25 pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Fix the capacit manner and ur Perform the fiv shown in the fo	nder the same e cycles accor	condition	is as (10).	atments
				[B1, B3, R1, R6, R7, E4] W.V. : 25Vmin. : 0.025max. W.V. : 16/10V : 0.035max.	Set for 24±2 h hours (high die measure.	lectric constan	it type) a	t room tempera	ture, then
15	Temperature	Q/D.F.	30pF and over : Q≧1000 30pF and below : D.F. Q≧400+20C	W.V. : 6.3V/4V : 0.05max. (C<3.3µF)	Step	1	2	3	4
	Cycle			: 0.1max. (C≥3.3µF) [F1, F5]	Temp. (℃)	Min. Operating Temp.+0/-3	Room Temp.	Max. Operating Temp.+3/-0	Room Temp.
			C : Nominal Capacitance (pF)	W.V. : 25Vmin. : 0.05max. (C<0.1µF)	Time (min.)	30±3	2 to 3	30±3	2 to 3
		I.R.	More than 10,000MΩ or 500Ω •	: 0.09max. (C≧0.1µF) W.V. : 16V/10V : 0.125max. W.V. : 6.3V : 0.15max. P F (Whichever is smaller)	 Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48±4 hours. Perform the initial measurement. 				
	-	Dielectric Strength	No defects						
			The measured and observed ch specifications in the following ta						
		Appearance	No defects or abnormalities						
		Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	B1, B3, R1, R6, R7, C8 : Within ±12.5% F1, F5 : Within ±30%					
16	Humidity 16 (Steady State)	Q/D.F.	30pF and over : Q≧350 10pF and over 30pF and below : Q≧275+2.5C 10pF and below : Q≧200+10C C : Nominal Capacitance (pF)	$\begin{array}{l} [B1, B3, R1, R6, R7, E4]\\ W.V.: 25Vmin.: 0.05max.\\ W.V.: 16/10V: 0.05max.\\ W.V.: 6.3V/4V\\ : 0.075max. (C<3.3\muF)\\ : 0.125max. (C\geq3.3\muF)\\ [F1, F5]\\ W.V.: 25Vmin.\\ : 0.075max. (C<0.1\muF)\\ : 0.125max. (C\geq0.1\muF)\\ W.V.: 16V/10V: 0.15max.\\ W.V.: 6.3V: 0.2max.\\ \end{array}$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$			perature compe	ensating
		I.R.	More than 1,000M Ω or 50 $\Omega \bullet F$	(Whichever is smaller)					

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			Specifi	ications	
No.	Ite	em	Temperature Compensating Type	High Dielectric Type	Test Method
			The measured and observed ch specifications in the following ta		
		Appearance	No defects or abnormalities		_
		Capacitance Change	Within \pm 7.5% or \pm 0.75pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4 : Within ±30% [W.V. : 10Vmax.] F1, F5 : Within +30/-40%	Apply the rated voltage at $40\pm2^{\circ}$ C and 90 to 95% humidity for 500±12 hours. Remove and set for 24±2 hours (temperature
17	Humidity Load	Q/D.F.	30pF and over : Q≧200 30pF and below : Q≧100+10C/3 C : Nominal Capacitance (pF)	$ \begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.05max. \\ W.V.: 16/10V: 0.05max. \\ W.V.: 6.3V \\ : 0.075max. (C<3.3\mu F) \\ : 0.125max. (C\geq3.3\mu F) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.075max. (C<0.1\mu F) \\ : 0.125max. (C\geq0.1\mu F) \\ W.V.: 16V/10V: 0.15max. \\ W.V.: 6.3V: 0.2max. \\ \end{array} $	 compensating type) or 48±4 hours (high dielectric constant type) at room temprature, then muasure. The charge/discharge current is less than 50mA. Initial measurement for F1, F5/10V max. Apply the rated DC voltage for 1 hour at 40±2°C. Remove and set for 48±4 hours at room temperature. Perform initial measurement.
		I.R.	More than 500M Ω or 25 Ω • F (V	Whichever is smaller)	
			The measured and observed ch specifications in the following ta	,	
		Appearance	No defects or abnormalities		
		Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4 : Within ±30% [Exept 10Vmax. and. C≧1.0μF] F1, F5 : Within +30/−40% [10Vmax. and. C≧1.0μF]	Apply 200% of the rated voltage at the maximum operating temperature ±3°C for 1000±12 hours. Set for 24±2 hours (temperature compensating type) or 48±4 hours (high dielectric constant type) at room temperature.
18	High Temperature Load	Q/D.F.	30pF and over : Q≥350 10pF and over 30pF and below : Q≥275+2.5C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	$eq:started_st$	 temperature, then measure. The charge/discharge current is less than 50mA. Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage at the maximun operating temperature ±3°C for one hour. Remove and set for 48±4 hours at room temperature. Perform initial measurement.
		I.R.	More than 1,000M Ω or 50 Ω •F (

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Table A-1

		Capacitance Change from 25°C (%)							
Char.	Nominal Values (ppm/℃)*1	-55		-	30	-10			
		Max.	Min.	Max.	Min.	Max.	Min.		
5C	0± 30	0.58	-0.24	0.40	-0.17	0.25	-0.11		
6C	0± 60	0.87	-0.48	0.59	-0.33	0.38	-0.21		
6P	-150± 60	2.33	0.72	1.61	0.50	1.02	0.32		
6R	-220± 60	3.02	1.28	2.08	0.88	1.32	0.56		
6S	-330 ± 60	4.09	2.16	2.81	1.49	1.79	0.95		
6T	-470± 60	5.46	3.28	3.75	2.26	2.39	1.44		
7U	-750±120	8.78	5.04	6.04	3.47	3.84	2.21		
1X	+350 to -1000	_	-	_	_	-	_		

*1Nominal values denote the temperature coefficient within a range of 25°C to 125°C (for Δ C)/85°C (for other TC).

			(Capacitance Cha	ange from 20°C (%))	
Char.	Nominal Values (ppm/℃)*2	-	-55	-	-25	-	-10
	-	Max.	Min.	Max.	Min.	Max.	Min.
2C	0± 60	0.82	-0.45	0.49	-0.27	0.33	-0.18
3C	0±120	1.37	-0.90	0.82	-0.54	0.55	-0.36
4C	0±250	2.56	-1.88	1.54	-1.13	1.02	-0.75
2P	-150± 60	_	-	1.32	0.41	0.88	0.27
3P	-150±120	-	-	1.65	0.14	1.10	0.09
4P	-150 ± 250	-	-	2.36	-0.45	1.57	-0.30
2R	-220 ± 60	-	-	1.70	0.72	1.13	0.48
3R	-220±120	-	-	2.03	0.45	1.35	0.30
4R	-220±250	-	-	2.74	-0.14	1.83	-0.09
2S	-330 ± 60	-	-	2.30	1.22	1.54	0.81
3S	-330±120	-	-	2.63	0.95	1.76	0.63
4S	-330±250	-	-	3.35	0.36	2.23	0.24
2T	-470± 60	-	-	3.07	1.85	2.05	1.23
3T	-470±120	-	-	3.40	1.58	2.27	1.05
4T	-470 ± 250	_	_	4.12	0.99	2.74	0.66
3U	-750±120	-	-	4.94	2.84	3.29	1.89
4U	-750±250	_	-	5.65	2.25	3.77	1.50

*2Nominal values denote the temperature coefficient within a range of 20°C to 125°C (for Δ C)/85°C (for other TC).

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

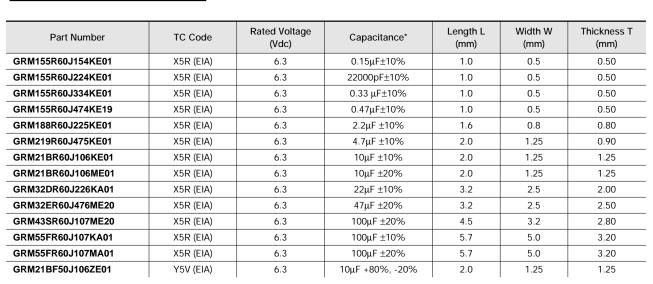
High Dielectric Constant Type 100V

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM188R72A222KD01	X7R (EIA)	100	2200pF±10%	1.6	0.8	0.80
GRM188R72A332KD01	X7R (EIA)	100	3300pF±10%	1.6	0.8	0.80
GRM219R72A472KA01	X7R (EIA)	100	4700pF±10%	2.0	1.25	0.90
GRM219R72A682KA01	X7R (EIA)	100	6800pF±10%	2.0	1.25	0.90
GRM21BR72A103KA01	X7R (EIA)	100	10000pF±10%	2.0	1.25	1.25
GRM31MR72A333KA01	X7R (EIA)	100	33000pF±10%	3.2	1.6	1.15
GRM31MR72A473KA01	X7R (EIA)	100	47000pF±10%	3.2	1.6	1.15
GRM32NR72A683KA01	X7R (EIA)	100	68000pF±10%	3.2	2.5	1.35
GRM32NR72A104KA01	X7R (EIA)	100	0.1µF±10%	3.2	2.5	1.35
GRM43RR72A154KA01	X7R (EIA)	100	0.15µF±10%	4.5	3.2	1.80
GRM43RR72A224KA01	X7R (EIA)	100	22000pF±10%	4.5	3.2	1.80
GRM43DR72A474KA01	X7R (EIA)	100	0.47µF±10%	4.5	3.2	2.00
GRM55DR72A105KA01	X7R (EIA)	100	1μF ±10%	5.7	5.0	2.00
GRM188F52A472ZD01	Y5V (EIA)	100	4700pF +80%, -20%	1.6	0.8	0.80
GRM32NF52A104ZA01	Y5V (EIA)	100	10000pF +80%, -20%	3.2	2.5	1.35
GRM55RF52A474ZA01	Y5V (EIA)	100	0.47µF +80%, -20%	5.7	5.0	1.80

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

Thin Layer Large-Capacitance type

Part Number		Dime	nsions (mi	n)		
Fait Number	L	W	T	e min.	g min.	
GRM033	0.6 ±0.03	0.3 ±0.03	0.3 ±0.03	0.1 to 0.2	0.2	
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	. 4
GRM185	1.6 ±0.1	0.8 ±0.1	0.5 +0/-0.2	0.2 to 0.5	0.5	_*
GRM188	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5	· •
GRM216			0.6 ±0.1			
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7	
GRM21B			1.25 ±0.1			
GRM316			0.6 ±0.1			
GRM319	3.2 ±0.15	1.6 ±0.15	0.85 ±0.1	0.3 to 0.8	1.5	е
GRM31M	1		1.15 ±0.1	0.3 10 0.8	1.5	-
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			
GRM32D	3.2 ±0.3	2.5 +0.2	2.0 ±0.2	0.3	1.0	
GRM32E	1 3.2 ±0.3	2.5 <u>1</u> 0.2	2.5 ±0.2	0.5	1.0	
GRM43D			2.0 ±0.2			
GRM43E	4.5 ±0.4	3.2 ±0.3	2.5 ±0.2	0.3	2.0	
GRM43S	1		2.8 ±0.2			
GRM55F	5.7 ±0.4	5.0 ±0.4	3.2 ±0.2	0.3	2.0	



No.	Iter	m	S		Test Method					
1	Operating Temperature Range		B1, B3, F1 : -25°C to +88 R6 : -55°C to +85°C F5 : -30°C to +85°C C8 : -55°C to +105°C, C7			eference Temperature : 25°C 31, B3, F1 : 20°C)				
2	Rated Voltage		See the previous pages		may be ap When AC whichever	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V ^{P.P} or V whichever is larger, should be maintained within the rated voltage range.				
3	Appearance	се	No defects or abnormalities		Visual insp	Visual inspection				
4	Dimension	ns	Within the specified dime	nsions	Using calip	pers				
5	Dielectric Strength		No defects or abnormaliti	es	is applied I	No failure should be observed when 250% of the rated vo is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.				
6	Insulation Resistance		More than 50 Ω • F		not exceed 75%RH ma	The insulation resistance should be measured with a DC voltage not exceeding the rated voltage at Reference Temperature and 75%RH max. and within 1 minutes of charging, provided the charge/discharge current is less than 50mA.				
			Within the specified tolera	ance		The capacitance should be measured at Reference Temperature at the frequency and voltage shown in the tabl				
7	Capacitan	ce		*Table 1 GRM155 B3/R6 1A 124 to 224 GRM185 B3/R6 1A 105 GRM188 B3/R6 1C/1A 225 GRM219 B3/R6 1A 475	- C≦10 - C≦10 - C>10		Frequency 1±0.1kHz 1±0.1kHz 120±24Hz	Voltage 1.0±0.2Vrms 0.5±0.1Vrms 0.5±0.1Vrms		
			B1, B3, R6, C7, C8 : 0.1 F1, F5 : 0.2 max.	GRM21B B3/R6 1C/1A 106	_ iter The D.F. s frequency	items on the left side. The D.F. should be measured at Reference Temperature at th frequency and voltage shown in the table.				
8	Dissipation (D.F.)	n Factor		*Table 1 GRM155 B3/R6 1A 124 to 224 GRM185 B3/R6 1A 105 GRM188 B3/R6 1C/1A 225 GRM219 B3/R6 1A 475 GRM21B B3/R6 1C/1A 106	C≦10 C≦10 C≥10 C>10 ×1 Ho	Capacitance Frequency C≤10µF (10V min.)*1 1±0.1kHz C≤10µF (6.3V max.) 1±0.1kHz C>10µF 120±24Hz *1 However the Voltage is 0.5+/−0.1\ items on the left side.		1.0±0.2Vrms 0.5±0.1Vrms 0.5±0.1Vrms		
		No bias	R6 : Within +/-15% F5 : Within +22/-82° C7 : Within +/-22%	% (−25°C to +85°C)	each speci The ranges Reference shown in th In case of measured equilibration	The capacitance change should be measured after 5min. at each specified temp. stage. The ranges of capacitance change compared with the Reference Temperature value over the temperature ranges shown in the table should be within the specified ranges.* In case of applying voltage, the capacitance change should I measured after 1 more min. with applying voltage in equilibration of each temp. stage. *GRM43 B1/R6 0J/1A 336/476 only : 1.0±0.2Vrms				
	-				Step	Temperatur	те (°С)	Applying Voltage (V)		
9	Capacitance Temperature	50% of the Rated Voltage	$E_1^{(1)}$ Within $\pm 30/-95\%$	12	Reference Ten -55±3 (for R -25±3 (for B -30±3 (f	6, C7, C8)/ 1, B3, F1)				
	Characteristics			3	Reference Ten	npereture±2	No bias			
				4	85±3 (for B1, B3 125±3 (fo 105±3 (fo	or C7)/				
				5	20±	2				
				6	-25±3 (for		50% of the rated			
				78	20±		voltage			
					 Initial mea Perform a 	85 ± 3 (for asurement for hig heat treatment at r 48±4 hours at n	h dielectric cor 150 +0/-10°0	C for one hour and		

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No.	Item	Specifications		Test Method				
		No removal of the terminations or other defects should occur	Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 1a using an eutectic solder. Then apply $10N^*$ force in parallel with the test jig for $10+/-1$ sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. *5N : GR \Box 15/GRM18, 2N : GR \Box 33					
10	Adhesive Strength of Termination	Solder resist Baked electrode or copper foil	Type GR□03 GR□15 GRM18 GRM21 GRM31 GRM31	a 0.3 0.4 1.0 1.2 2.2	b 0.9 1.5 3.0 4.0 5.0	c 0.3 0.5 1.2 1.65 2.0		
		Fig. 1a	GRM32 GRM43 GRM55	2.2 3.5 4.5	5.0 7.0 8.0	2.9 3.7 5.6		
	Appearance No defects or abnormalities		Solder the capacit	or on the test ji	ig (glass epoxy	board) in the		
11	Capacitance Vibration D.F.	Within the specified tolerance B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 55Hz. The frequency range, from 10 to 55Hz and return to 10Hz, should be traversed in approximately 1 minute. This motion should be applied for a period of 2 hours in each 3 mutually perpendicular directions (total of 6 hours).					
		No cracking or marking defects should occur	Solder the capacit in Fig. 2a using an direction shown in be done either with should be conduct and free of defects	eutectic solde Fig. 3a for 5+, an iron or usi ed with care so	r. Then apply a /-1 sec. The s ng the reflow r o that the solde	a force in the oldering should nethod and		
12	Deflection	ction 45 45 45		$ \begin{array}{c} & & \\ & & \\ \hline \\$				
				1		R□15 : t : 0.8mm)		
		Fig.3a	Type GR⊡03	0.3	b 0.9	с 0.3		
			<u></u> GR⊡15	0.3	1.5	0.3		
			GRM18	1.0	3.0	1.2		
			GRM21	1.2	4.0	1.65		
			GRM31	2.2	5.0	2.0		
			GRM32	2.2	5.0	2.9		
			GRM43	3.5	7.0	3.7		
			GRM55	4.5	8.0	5.6		
						(in mm)		
13	Solderability of Termination	75% of the terminations is to be soldered evenly and continuously	Immerse the capacitor in a solution of ethanol (JIS-K-8101) an rosin (JIS-K-5902) (25% rosin in weight propotion). Preheat at 80 to 120°C for 10 to 30 seconds. After preheating, immerse in an eutectic solder solution for 2+/-0.5 seconds at 230+/-5°C.					

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No.	Item Specifications			Test Method						
	Appearance Capacitance Change Q/D.F.	No defects or abnormalities B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20% B1, B3, R6, C7, C8 : 0.1 max.	Immerse the c 270+/−5℃ for 24+/−2 hours	Preheat the capacitor at 120 to 150°C for 1 minute. Immerse the capacitor in an eutectic solder solution at 270+/-5°C for 10+/-0.5 seconds. Set at room temperature fo 24+/-2 hours (temperature compensating tyoe) or 48+/-4 hours (high dielectric constant type), then measure.						
Resistan		F1, F5 : 0.2 max.	Initial measurements	Initial measurement for high dielegtric constant type						
14 to Solderin Heat		More than 50Ω • F No defects	Perform a hea then set at roo	Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48+/-4 hours. Perform the initial measurement. *Preheating for GRM32/43/55						
			*Preheating for							
			Step	Temp	oerature	Т	Time			
			1 100°C to 120°C 2 170°C to 200°C				1 min.			
	Appearance	No defects or abnormalities	Fix the capaci	Fix the capacitor to the supporting jig in the same manner a						
	Capacitance Change	B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20%	Perform the fi	under the same conditions as (10). Perform the five cycles according to the four heat treatments shown in the following table. Set for 24+/-2 hours (temperature compensating type) or 48+/-4 hours (high dielectric constant type) at room						
	D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	Set for 24+/-							
	I.R.	More than 50Ω • F	temperature,	then measure.						
Temperatu 15 Sudden Change	re Dielectric Strength	No defects	Step	1 Min.	2 Room	3 Max.	4 Room			
Change			Temp. (℃) 	Operating Temp. +0/-3 30±3	Tomp	Operating Temp. +3/-0 30±3	Tomp			
	Appearance Capacitance Change	No defects or abnormalities B1, B3, R6, C7, C8 : Within ±12.5% F1, F5 : Within ±30%	Perform a hea then set at roc Perform the in Apply the rate	rement for high dielectric constant type at treatment at $150+0/-10^{\circ}$ C for one hour and om temperature for $48+/-4$ hours. hitial measurement. In voltage at $40+/-2^{\circ}$ C and 90 to 95% humidit urs. The charge/discharge currentis less than						
High Temperatu High Humidity (Steady)		B1, B3, R6, C7, C8 : 0.2 max. F1, F5 : 0.4 max. More than 12.5Ω • F	Perform a heat then let sit for	 Initial measurement Perform a heat treatment at 150+0/-10°C for one hour and then let sit for 48+/-4 hours at room temperature. Perform the initial measurement. Measurement after test Perform a heat treatment at 150+0/-10°C for one hour and then let sit for 48+/-4 hours at room temperature, then measure. 						
(oroady)			Perform a hea then let sit for							
	Appearance	No defects or abnormalities			-	000+/-12 hou				
	Capacitance Change	B1, B3, R6, C7, C8 : Within ±12.5% F1, F5 : Within ±30%	hours at room	 maximum operating temperature +/-3°C. Let sit for 48+/-4 hours at room temperature, then measure. The charge/ discharge current is less than 50mA. Initial measurement Perform a heat treatment at 150+0/-10°C for one hour and then let sit for 48+/-4 hours at room temperature. Perform the initial measurement. 						
	D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.4 max.	•Initial measu							
17 Durabili	^y I.R.	More than 25Ω • F	then let sit for							
				t treatment at		10℃ for one ho temperature, th				